NXPSC10650X



Silicon Carbide Diode

Rev.03 - 06 May 2020

#### **Product data sheet**

### **1. General description**

Silicon Carbide Schottky diode in a TO220F-2L plastic package, designed for high frequency switched-mode power supplies.



### 2. Features and benefits

- · Highly stable switching performance
- High forward surge capability I<sub>FSM</sub>
- · Extremely fast reverse recovery time
- Superior in efficiency to Silicon Diode alternatives
- Reduced losses in associated MOSFET
- Reduced EMI
- Reduced cooling requirements
- RoHS compliant
- Insulated package rated at 2500V RMS

### 3. Applications

- Power factor correction
- Telecom / Server SMPS
- UPS
- PV inverter
- PC Silverbox
- LED / OLED TV
- Motor Drives

## 4. Quick reference data

Table 1. Q	uick reference data						
Symbol	Parameter		Unit				
Absolute	maximum rating						
$V_{\text{RRM}}$	repetitive peak reverse voltage		650			V	
$I_{F(AV)}$	average forward current	δ = 0.5 ; square-wave pulse; T <sub>h</sub> ≤ 25 °C; Fig. 1; Fig. 2; Fig. 3	10			A	
T <sub>j</sub>	junction temperature			1	75		°C
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static ch	aracteristics						
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 10 A; T <sub>j</sub> = 25 °C; <u>Fig. 5</u>		-	1.5	1.7	V
		I <sub>F</sub> = 10 A; T <sub>j</sub> = 150 °C; <u>Fig. 5</u>		-	1.8	2.1	V
Dynamic	characteristics	·					
Q <sub>r</sub>	recovered charge	$I_F = 10 \text{ A}; \text{ d}I_F/\text{d}t = 500 \text{ A}/\mu\text{s}; \text{ V}_R = 400 \text{ V};$ $T_j = 25 \text{ °C}; \text{ Fig. 7}$		-	16	-	nC

# 5. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode		K IA A
2	А	anode	oOo	K <u>– K</u> 001aaa020
mb	n.c.	mounting base; isolated		

## 6. Ordering information

Table 3. Ordering information											
Type number	Package name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date					
NXPSC10650X	TO220F-2L	NXPSC10650X6Q	Tube	50	TO220FN-2L	20-Jul-2016					

# 7. Marking

Table 4. Marking codes	
Type number	Marking codes
NXPSC10650X	NXPSC 10650X

## 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
$V_{\text{RRM}}$	repetitive peak reverse voltage		650	V
$V_{\text{RWM}}$	crest working reverse voltage		650	V
V <sub>R</sub>	reverse voltage	DC	650	V
$I_{F(AV)}$	average forward current	δ = 0.5; square-wave pulse; T <sub>h</sub> ≤ 25 °C; Fig. 1; Fig. 2; Fig. 3	10	A
I <sub>FRM</sub>	repetitive peak forward current	δ = 0.5; t <sub>p</sub> = 25 μs; T <sub>h</sub> ≤ 25 °C; square-wave pulse	20	A
I <sub>FSM</sub>	non-repetitive peak	$t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse	50	A
	forward current	$t_p$ = 10 µs; $T_{j(init)}$ = 25 °C; square-wave pulse	450	А
l <sup>2</sup> t	I <sup>2</sup> t for fusing	sine-wave pulse; $T_{j(init)}$ = 25 °C; $t_p$ = 10 ms	12.5	A <sup>2</sup> s
T <sub>stg</sub>	storage temperature		-55 to 175	°C
T <sub>j</sub>	junction temperature		175	°C

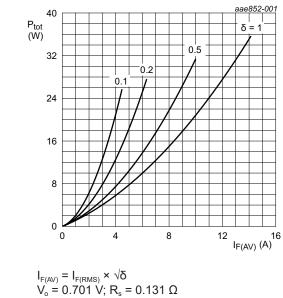
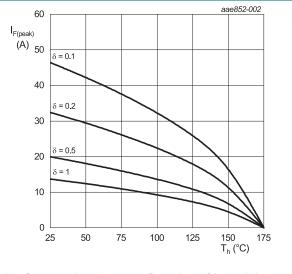
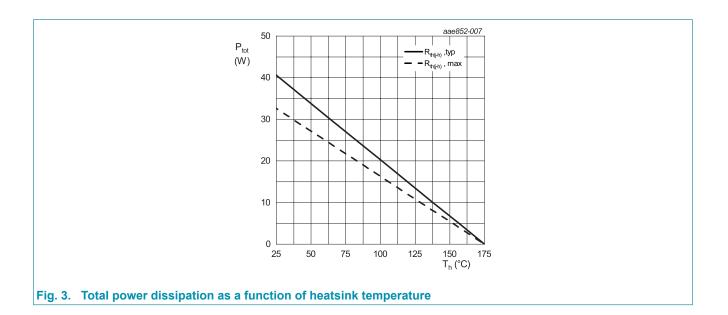


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values









## 9. Thermal characteristics

Table 6. Th	ermal characteristics		 			
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to heatsink	with heatsink compound; Fig. 4	-	3.7	4.6	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient free air	in free air	-	55	-	K/W

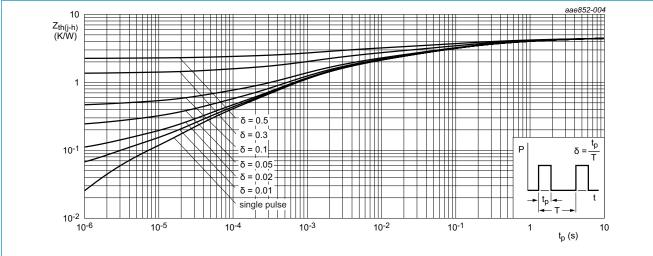


Fig. 4. Transient thermal impedance from junction to heatsink as a function of pulse duration

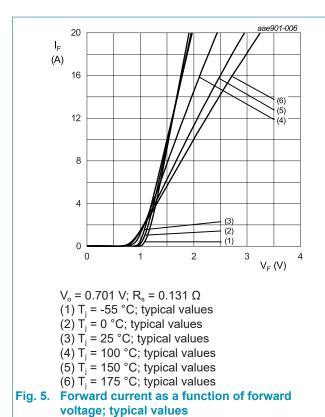
## **10. Isolation characteristics**

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Table 7. Iso	plation characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>isol(RMS)</sub>	RMS isolation voltage	50 Hz $\leq$ f $\leq$ 60 Hz; RH $\leq$ 65 %; from all pins to external heatsink; sinusoidal waveform; clean and dust free	-	-	2500	V

## **11. Characteristics**

Table 8. C	haracteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
$V_{\rm F}$	forward current	I <sub>F</sub> = 10 A; T <sub>j</sub> = 25 °C; <u>Fig. 5</u>	-	1.5	1.7	V
		I <sub>F</sub> = 10 A; T <sub>j</sub> = 150 °C; <u>Fig. 5</u>	-	1.8	2.1	V
I <sub>R</sub>	reverse current	V <sub>R</sub> = 650 V; T <sub>j</sub> = 25 °C; <u>Fig. 6</u>	-	-	60	μA
		V <sub>R</sub> = 650 V; T <sub>j</sub> = 150 °C; <u>Fig. 6</u>	-	-	240	μA
Dynamic	characteristics	· · · · ·	i	<b>I</b>		
Q <sub>r</sub>	recovered charge	I <sub>F</sub> = 10 A; V <sub>R</sub> = 400 V; dI <sub>F</sub> /dt = 500 A/μs; T <sub>j</sub> = 25 °C; <u>Fig. 7</u>	-	16	-	nC
C <sub>d</sub>	diode capacitance	f = 1 MHz; V <sub>R</sub> = 1 V; T <sub>j</sub> = 25 °C	-	328	-	pF
		f = 1 MHz; V <sub>R</sub> = 300 V; T <sub>j</sub> = 25 °C	-	44	-	pF
		f = 1 MHz; V <sub>R</sub> = 600 V; T <sub>j</sub> = 25 °C	-	42	-	pF
E <sub>as</sub>	non-repetitive	I <sub>R</sub> = 5.5 A; L = 5 mH; T <sub>j(init)</sub> = 25 °C	75	-	-	mJ
	avalanche energy					



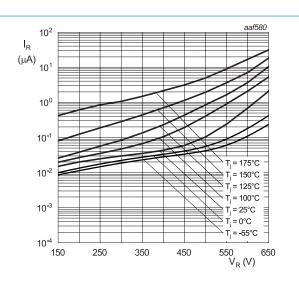
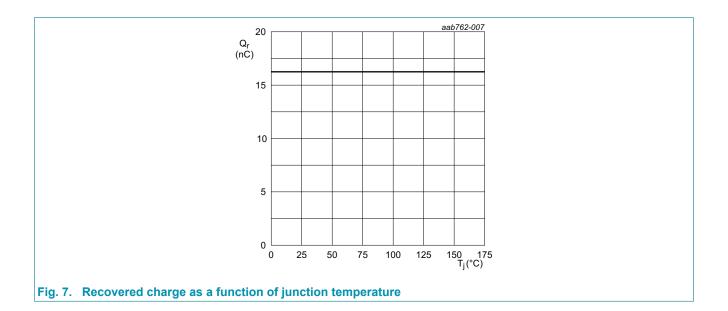


Fig. 6. Reverse leakage current as a function of reverse voltage; typical value

### **WeEn Semiconductors**



# 12. Package outline

				ugh-ho	e pac	kage; i	solated	heatsin	k mour	nted; 1	mountir	ıg ho <b>l</b> e;	2-lead	I TO-22	20F	TO22
	min 4.35 2.40 0.76 1.22 0.46 15.95 9.00 5.08 10.05 13.15 3.15 0.50 2.95 3.40 2.30					 										
														_		
Unit A A1 b b1 c D D1 e E L L1 L2 P q Q	$m_{0} \times [4.65] 2.80 0.89 1.60 0.59 16.25 9.30 (typ) 10.35 13.85 3.45 1.00 3.25 (typ) 2.80 ]$	Unit A	A1	b	b1	с	D	D1	е	Е	L	L1	L2	Р	P	Q
min 4 35 2 40 0 76 1 22 0 46 15 95 9 00 10 05 13 15 3 15 0 50 2 95 2 30			_													

NXPSC10650X
Product data sheet

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## 13. Legal information

#### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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### 14. Contents

1. General description	1
2. Features and benefits	1
3. Applications	1
4. Quick reference data	1
5. Pinning information	2
6. Ordering information	2
7. Marking	2
8. Limiting values	3
9. Thermal characteristics	5
10. Isolation characteristics	5
11. Characteristics	6
12. Package outline	8
13. Legal information	9
14. Contents	

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